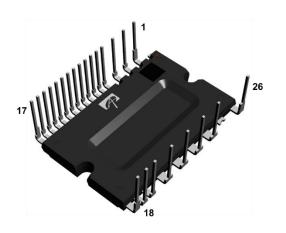


AIP3D20A060Q4(N) AIP3P20A060Q4(N) Dual-In-Line Package Intelligent Power Module

External View



Size: 38 x 24 x 3.6 mm



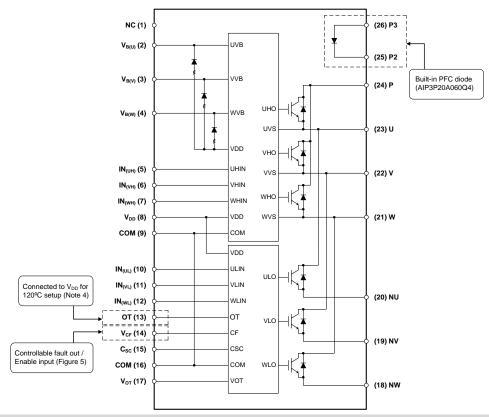
Features

- UL Recognized: UL 1775 File E345245
- 3-phase inverter module with optional built-in PFC diode
- 600V-20A (Trench Shielded Planar Gate IGBT)
- Low V_F and Ultra-fast recovery diode for PFC (AIP3P20A060Q4)
- Built-in bootstrap diodes with integrated current-limiting resistor
- Control supply under-voltage lockout protection (UVLO)
- Controllable over-temperature protection (OT)
- Temperature monitoring (Vot)
- Short-circuit current protection (Csc)
- Controllable fault out signal (V_{CF}) corresponding to SC, UV and OT fault
- Enable input functionality: Low-side IGBTs shut-down
- Input interface: 3 and 5V line, Schmitt trigger receiver circuit (Active high)
- Isolation ratings of 2000Vrms/min

Applications

- AC 100-240Vrms class low power motor drives
- Air-conditioners, Washing machines, Compressors and Fan Motors

Internal Equivalent Circuit / Pin Configuration





Ordering Information

Part Number	Temperature Range	Package	Terminal type
AIP3D20A060Q4	-40°C to 150°C	IPM-3	Long
AIP3D20A060Q4N	-40°C to 150°C	IPM-3A	Normal
AIP3P20A060Q4	-40°C to 150°C	IPM-3B	Long with PFC diode
AIP3P20A060Q4N	-40°C to 150°C	IPM-3C	Normal with PFC diode



AOS products are offered in packages with Pb-free plating and compliant to RoHS standards. Please visit <u>https://aosmd.com/sites/default/files/media/AOSGreenPolicy.pdf</u> for additional information.

Pin Description

Pin Number	Pin Name	Pin Function
1	NC	No Connection
2	V _{B(U)}	High-Side Bias Voltage for U-Phase IGBT Driving
3	V _{B(V)}	High-Side Bias Voltage for V-Phase IGBT Driving
4	V _{B(W)}	High-Side Bias Voltage for W-Phase IGBT Driving
5	IN _(UH)	Signal Input for High-Side U-Phase
6	IN _(VH)	Signal Input for High-Side V-Phase
7	IN _(WH)	Signal Input for High-Side W-Phase
8	V _{DD}	Common Bias Voltage for IC and IGBTs Driving
9	COM	Common Supply Ground
10	IN _(UL)	Signal Input for Low-Side U-Phase
11	IN _(VL)	Signal Input for Low-Side V-Phase
12	IN _(WL)	Signal Input for Low-Side W-Phase
13	OT	Controllable Over Temperature Protection (Connected to V _{DD} for 120°C setup)
14	Vcf	Controllable Fault Output
15	C _{SC}	Capacitor (Low-Pass Filter) for Short-circuit Current Detection Input
16	COM	Common Supply Ground
17	Vot	Voltage Output of LVIC Temperature
18	NW	Negative DC-Link Input for W-Phase
19	NV	Negative DC-Link Input for V-Phase
20	NU	Negative DC-Link Input for U-Phase
21	W	Output for W-Phase
22	V	Output for V-Phase
23	U	Output for U-Phase
24	Р	Positive DC-Link Input
25	P2	PFC Diode Cathode (AIP3P20A060Q4)
26	P3	PFC Diode Anode (AIP3P20A060Q4)



Absolute Maximum Ratings

 $T_J = 25^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	Ratings	Units
Inverter				
V _{PN}	Supply Voltage	Applied between P - NU,NV,NW	450	V
V _{PN(surge)}	Supply Voltage (surge)	Applied between P - NU,NV,NW	500	V
VCES	Collector-Emitter Voltage		600	V
1	Output Dhoop Output	Tc=25°C, TJ<150°C	20	А
lc	Output Phase Current	Tc=80°C, TJ<150°C	15	А
±Ірк	Output Peak Phase Current	Tc=25°C, less than 1ms pulse width	40	А
tsc	Short Circuit Withstand Time	V _{PN} ≤400V, TJ=150°C, V _{DD} =15V	5	μs
Pc	Collector Dissipation	T _C =25°C, per chip	56	W
TJ	Operating Junction Temperature		-40 to 150	°C
PFC Diode	3			
V _{RRM}	Repetitive peak Reverse Voltage	Applied between P2 – P3	650	V
		T _C =25°C, T _J <150°C	40	А
lF	Output Phase Current	T _C =100°C, T _J <150°C	20	А
Control (P	rotection)			
V _{DD}	Control Supply Voltage	Applied between V _{DD} -COM	25	V
V _{DB}	High-Side Control Bias Voltage	Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	25	V
VIN	Input Voltage	$\begin{array}{l} \mbox{Applied between IN}_{(UH), \ IN} (VH), \ IN}_{(WH), \ IN} (UL), \\ \mbox{IN}_{(VL), \ IN} (WL) - COM \end{array}$	-0.3 ~V _{DD} +0.3	V
Vcf	Fault Output Supply Voltage	Applied between VCF-COM	-0.3 ~ 5.5	V
ICF	Fault Output Current	Sink current at VCF terminal	1	mA
V _{SC}	Current Sensing Input Voltage	Applied between C _{SC} -COM	-0.3 ~ 5.5	V
Vot	Temperature Output	Applied between Vor-COM	-0.3 ~ 5.5	V
Total Syst	em			
Vpn(prot)	Self Protection Supply Voltage Limit (Short-Circuit Protection Capability)	V_{DD} =13.5-16.5V, Inverter part T _J =150°C, Non-repetitive, less than 2µs	400	V
Tc	Module Case Operation Temperature	Measurement point of T _c is provided in Figure 1	-30 to 125	°C
Tstg	Storage Temperature		-40 to 150	°C
Viso	Isolation Voltage	60Hz, sinusoidal, AC 1min, between connected all pins and heat sink plate	2000	Vrms

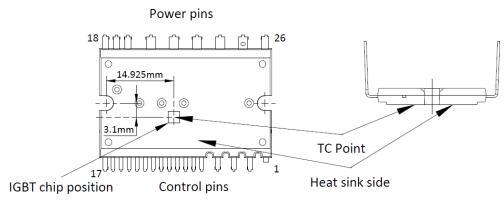


Figure 1. T_c Measurement Point



Thermal Resistance

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Rth(j-c)Q	Junction to Case Thermal Resistance ⁽¹⁾	Inverter IGBT (per 1/6 module)	-	-	2.23	K/W
Rth(j-c)F		Inverter FWD (per 1/6 module)	-	-	3.32	K/W
Rth(j-c)D		PFC Diode (AIP3P20A060Q4)	-	-	1.79	K/W

Note:

1. For the measurement point of case temperature (T_C), please refer to Figure 1.

Electrical Characteristics

 $T_J = 25^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Co	onditions	Min.	Тур.	Max.	Units
Inverter							
	Collector-Emitter Saturation	V _{DD} =V _{DB} =15V,	Ic=15A, TJ=25°C	-	1.50	2.00	V
Vce(sat)	Voltage	V _{IN} =5V	Ic=15A, TJ=125°C	-	1.75	-	V
VF	FWD Forward Voltage	V _{IN} =0	I _F =15A, T _J =25°C	-	1.6	2.10	V
ton				0.30	0.60	1.00	μs
tc(on)		Vpn=300V, Vdd=Vdb	=15V	-	0.20	0.40	μs
t _{OFF}	Switching Times	Ic=15A, TJ=25°C, VI		-	1.00	1.50	μs
tc(off)		Inductive load (high-	side)	-	0.10	0.30	μs
t _{rr}				-	0.10	-	μs
1	Collector-Emitter Leakage		T _J =25°C	-	-	1	mA
ICES	Current	Vce=Vces	T _J =125°C	-	-	10	mA
PFC Diode	9						
V _F	FWD Forward Voltage		I _F =30A, T _J =25°C	-	1.45	-	V
Trr	Reverse recovery time		-	85	-	ns	
Qrr	Reverse recovery Charge	T ₁ =25°C V _P =400V	-	0.57	-	uC	
Irr	Peak reverse recovery current	TJ=25°C, V _R =400V, I _F =30A, dI _F /dt=320A/us		-	10.6	-	А
Control (P	rotection)						
Iqdd	Quiescent V _{DD} Supply Current	V _{DD} =15V, IN _(UH,VH,WH,UL,VL,WL) =0V	VDD-COM	-	-	2.1	mA
Iqdb	Quiescent V _{DB} Supply Current	V _{DB} =15V, IN _(UH, VH, WH) =0V	$V_{B(U)}\text{-}U, \ V_{B(V)}\text{-}V, \ V_{B(W)}\text{-}W$	-	-	0.3	mA
V _{SC(ref)}	Short-Circuit Trip Level	$V_{DD}=15V^{(2)}$		0.455	0.48	0.505	V
UVdt	-	Trip Level		10.3	11.4	12.5	V
UVdr	Supply Circuit Under-Voltage	Reset Level		10.8	11.9	13.0	V
UVdbt	Protection	Trip Level		8.5	9.5	10.5	V
UVdbr		Reset Level		9.5	10.5	11.5	V
	Tomporature Output (3)		LVIC Temperature=90°C	2.67	2.77	2.86	V
Vot	Temperature Output ⁽³⁾		LVIC Temperature=25°C	0.8	1.05	1.3	V
ΟTτ	Over-Temperature	The OT Pin is	Trip Level	100	120	140	°C
OT _{HYS}	Protection ⁽⁴⁾	connected to V _{DD} or open	Hysteresis of Trip Reset	-	30	-	°C



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
Control (Protection)							
Vcfh		$V_{SC}=0V$, V_{CF} Circuit: $10k\Omega$ to 5V pull-up	4.9	-	-	V	
Vcfl	Fault Output Voltage	$V_{SC}=1V$, V_{CF} Circuit: $10k\Omega$ to 5V pull-up	-	-	0.5	V	
V _{CF+}	CF positive going threshold		-	1.9	2.2	V	
Vcf-	CF negative going threshold		0.8	1.1	-	V	
		Pull-up resistor only	20	-	-	μs	
t _{FO} Fault Output Pulse Width	Fault Output Pulse Width ⁽⁵⁾	Pull-up resistor with pull-down capacitor $(R_{CF}=2.2M\Omega, C_{CF}=1nF, 5V \text{ pull-up})^{(Figure 5)}$	-	1	-	ms	
lin	Input Current	V _{IN} =5V	-	0.72	-	mA	
V _{th(on)}	ON Threshold Voltage			2.3	2.6	V	
V _{th(off)}	OFF Threshold Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$,	0.8	1.2		V	
Vth(hys)	ON/OFF Threshold Hysteresis Voltage	IN _(VL) , IN _(WL) -COM	-	1.1	-	V	
VF(BSD)	Bootstrap Diode Forward Voltage	I _F =10mA Including Voltage Drop by Limiting Resistor ⁽⁶⁾	0.5	1.0	1.5	V	
RBSD	Built-in Limiting Resistance	Included in Bootstrap Diode	80	100	120	Ω	

Notes:

2. Short-circuit protection works only for low sides.

- 3. When temperature exceeds the protective level that the user defined, the controller (MCU) should stop the IPM. Temperature of LVIC vs. V_{OT} output characteristics is described in Figure 3.
- 4. When the LVIC temperature exceeds OT Trip temperature level (OT_T), OT protection is triggered and fault outputs. OT Trip level can be adjusted by pull-down resistors values as shown in the table below.

OT Pin	OT _T [°C]
10kΩ	Disable
100kΩ	130
400kΩ	110
V_{DD} or Open	120

- Fault signal (F_o) outputs when SC, UV or OT protection is triggered. F_o pulse width is different for each protection mode. At SC failure, F_o pulse width is fixed (minimum 20µs) or controlled by RC network (see Figure 5), but at UV or OT failure, F_o outputs continuously until recovering from UV or OT state.
- 6. The characteristics of bootstrap diodes are shown in Figure 2.

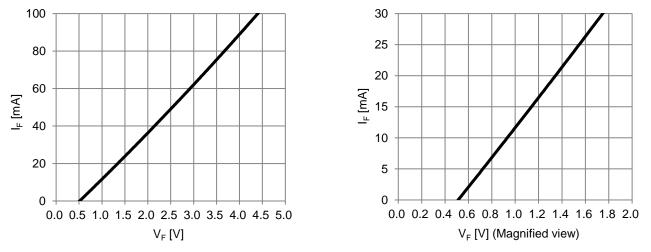


Figure 2. Built-in Bootstrap Diode VF-IF Characteristic (Tc=25°C)



AIP3D20A060Q4(N) / AIP3P20A060Q4(N)

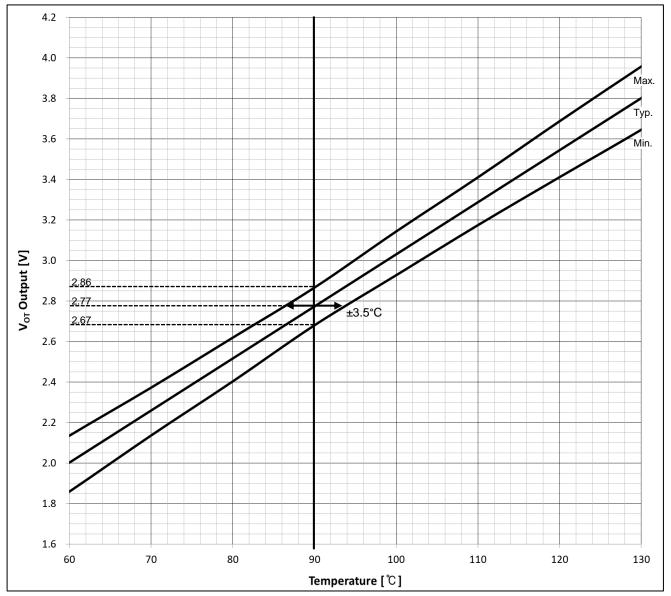
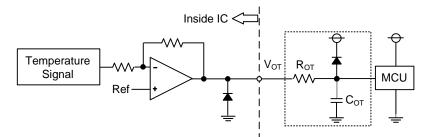


Figure 3. Temperature of LVIC vs. Vot Output Characteristics

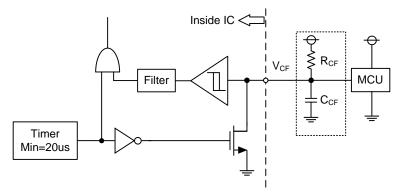


- (1) In the case of using V_{OT} with low voltage controller like 3.3V MCU, V_{OT} output might exceed control supply voltage 3.3V when temperature rises excessively. If system uses low voltage controller, it is recommended to insert a clamp diode between control supply of the controller and V_{OT} output for preventing over voltage destruction.
- (2) When V_{OT} is connected to MCU, to use RC ($R_{OT}=2k\Omega$, $C_{OT}=10nF$) filter is recommended.
- (3) In the case of not using V_{OT} , leave V_{OT} output NC (No connection).

Figure 4. Interface Circuit at Pin Vot

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- (1) The V_{CF} pin combines three functions in one pin: Fixed fault out, Controllable fault out pulse width based on RC network, and Enable input.
- (2) The V_{CF} pin provides an enable functionality that allows it to shut down the all low-side IGBTs. When the V_{CF} pin is in the high state the IPM is able to operate normally. If the V_{CF} pin is in a low state, the low-side IGBTs are turned off until the enable condition is restored. In addition, the V_{CF} pin can provide the fault output signal with the fixed or controlled fault out pulse width.
- (3) If a pull-up resistor ($10k\Omega$) only is connected to the V_{CF} pin, the fault output pulse width is fixed at minimum 20us.
- (4) If a capacitor (C_{CF}) is connected with a pull-up resistor (R_{CF}) together, the fault output pulse width can be controlled according to the resistor and the capacitor values. The length of fault output pulse width is determined by the following formula;
 - $t_{FO} = -(R_{CF}*C_{CF})*ln(1-V_{CF}+/V_{DD}) + 100ns + 20us(min.)$
 - ex) $V_{DD}=5V$, $R_{CF}=2.2M\Omega$, $C_{CF}=1nF$, $t_{FO}\approx1.07ms$. Recommended parameters in the design are C_{CF} of $\leq 1nF$ and R_{CF} of 0.1M to 2.2M Ω .

Figure 5. Interface Circuit at Pin VCF



Mechanical Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Mounting Torque	Mounting Screw: M3 (7)		0.59	0.69	0.78	Nm
Weight			-	9.12	-	g
Flatness	Refer to Figure 6		-50	-	100	μm

Note:

7. Plain washers (ISO 7089-7094) are recommended.

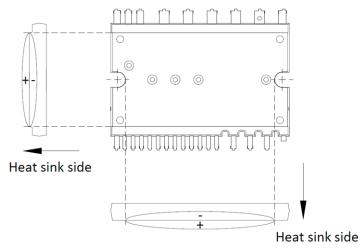


Figure 6. Flatness Measurement Positions

Recommended Operation Conditions

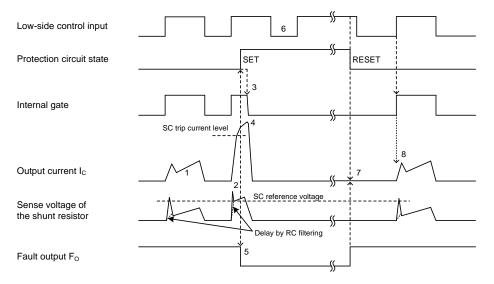
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{PN}	Supply Voltage	Applied between P-NU, NV, NW	0	300	450	V
Vdd	Control Supply Voltage	Applied between VDD-COM	13.5	15.0	16.5	V
V _{DB}	High-Side Bias Voltage	Applied between $V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	13.5	15.0	18.5	V
dV _{DD} /dt, dV _{DB} /dt	Control Supply Variation		-1	-	+1	V/µs
t _{dead}	Arm Shoot-Through Blocking Time	For each input signal	1.5	-	-	μs
fрwм	PWM Input Frequency	-40°C < T _J < 150°C	-	-	20	kHz
PWIN(ON)	Minimum Innut Dulas Midth (8)		0.5	-	-	μs
PWIN(OFF)	Minimum Input Pulse Width ⁽⁸⁾		0.5	-	-	μs
СОМ	COM Variation	Between COM-NU, NV, NW (including surge)	-5.0	-	5.0	V

Note:

8. IPM may not respond if the input pulse width is less than $PW_{IN(ON)}$, $PW_{IN(OFF)}$.

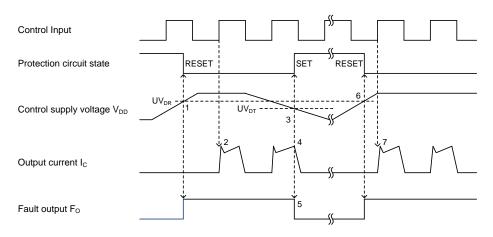


Time Charts of the IPM Protective Function



- (1) Normal operation: IGBT turns on and outputs current.
- (2) Short-circuit current detection (SC triggered).
- (3) All low-side IGBTs' gates are hard interrupted.
- (4) All low-side IGBTs turn OFF.
- (5) F_O output time (t_{FO})=minimum 20µs.
- (6) Input = "L" : IGBT OFF.
- (7) Fault output finishes, but output current will not turn on until next ON signal (L \rightarrow H).
- (8) Normal operation: IGBT turns on and outputs current.

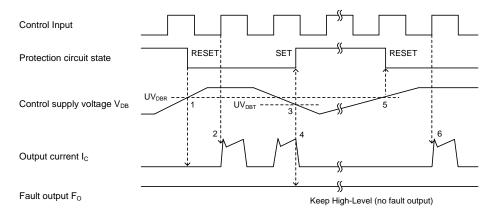
Figure 7. Short-Circuit Protection (Low-side Operation Only with the External Shunt Resistor and RC Filter)



- (1) Control supply voltage V_{DD} exceeds under voltage reset level (UV_{DR}), but IGBT turns on by next ON signal (L \rightarrow H).
- (2) Normal operation: IGBT turns on and outputs current.
- (3) V_{DD} level drops to under voltage trip level (UV_{DT}).
- (4) All low-side IGBTs turn OFF regardless of control input condition.
- (5) F_O output time (t_{FO})=minimum 20µs, and F_O stays low as long as V_{DD} is below UV_{DR}.
- (6) V_{DD} level reaches UV_{DR} .
- (7) Normal operation: IGBT turns on and outputs current.

Figure 8. Under-Voltage Protection (Low-side, UV_D)





(1) Control supply voltage V_{DB} rises. After the voltage reaches under voltage reset level UV_{DBR}, IGBT turns on by next ON signal (L \rightarrow H).

(2) Normal operation: IGBT turns on and outputs current.

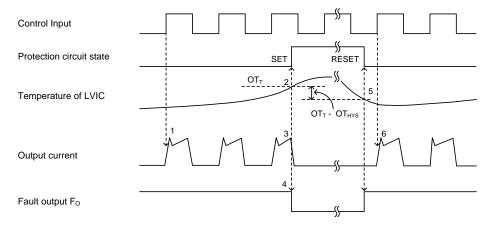
(3) V_{DB} level drops to under voltage trip level (UV_{DBT}).

(4) All high-side IGBTs turn OFF regardless of control input condition, but there is no Fo signal output.

(5) V_{DB} level reaches UV_{DBR} .

(6) Normal operation: IGBT turns on and outputs current.

Figure 9. Under-Voltage Protection (High-side, UVDB)



(1) Normal operation: IGBT turns on and outputs current.

(2) LVIC temperature exceeds over-temperature trip level (OT_T).

(3) All low-side IGBTs turn off regardless of control input condition.

(4) F_0 output time (t_{F0})=minimum 20µs, and F_0 stays low as long as LVIC temperature is over OT_T.

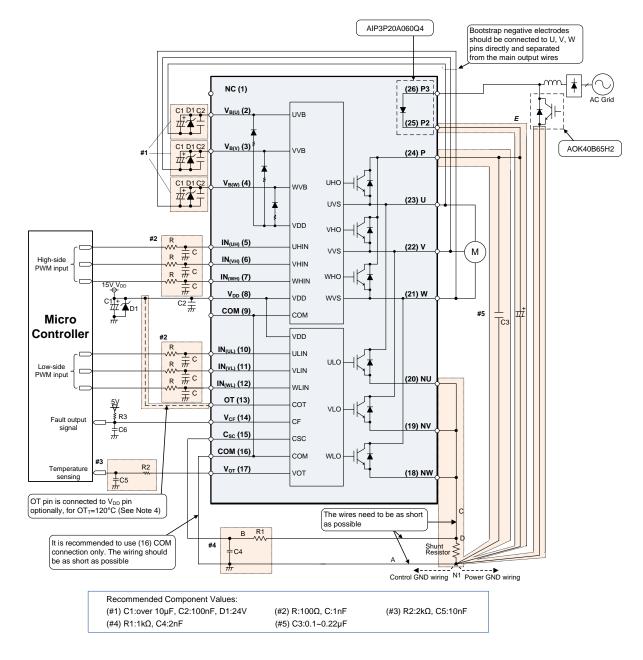
(5) LVIC temperature drops to over-temperature reset level (OT_T - OT_{HYS}).

(6) Normal operation: IGBT turns on by the next ON signal ($L \rightarrow H$).

Figure 10. Over-Temperature Protection (Low-side, Detecting LVIC Temperature)

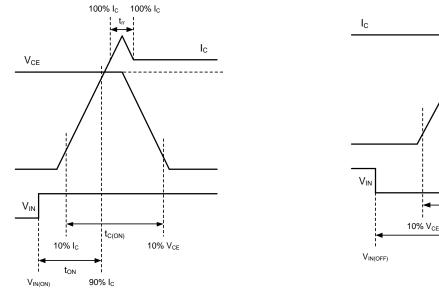


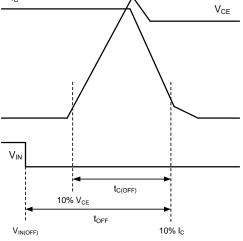
Example of Application Circuit



- (1) GND pattern: The star ground design is recommended. GND pattern should be separated at the one point of the shunt resistors.
- (2) COM pin: It is recommended to only use the (16) COM pin to minimize SC detection noise. Leave pin (9) NC (No Connection).
- (3) A Zener diode D1 (24V/1W) is recommended between each pair of control supply pins to prevent surge destruction.
- (4) Snubber capacitor: The wiring between the IPM and snubber capacitor (C3) including the shunt resistors should be as short as possible.
- (5) C_{SC} pin circuit: C4 should be placed as close to C_{SC} pin and COM (16) pin as possible to prevent protection function errors.
- (6) P2 pin connection: The pin P2 (PFC diode cathode) should connected directly to the positive terminal of DC-link capacitor as shown in the trace E.
- (7) Bootstrap capacitors: It is recommended that all capacitors are mounted as close to the IPM as possible.
- (8) Input circuit: The R and C filter circuit should be mounted to reduce input signal noise by high speed switching. C should be placed as close to COM (16) pin as possible.
- (9) V_{CF} pin circuit: V_{CF} output is open drain type. The signal line should be pulled up to the positive side of the 5V/3.3V logic power supply with a proper resistor R3. For the detailed design guide, please refer to the Figure 5.







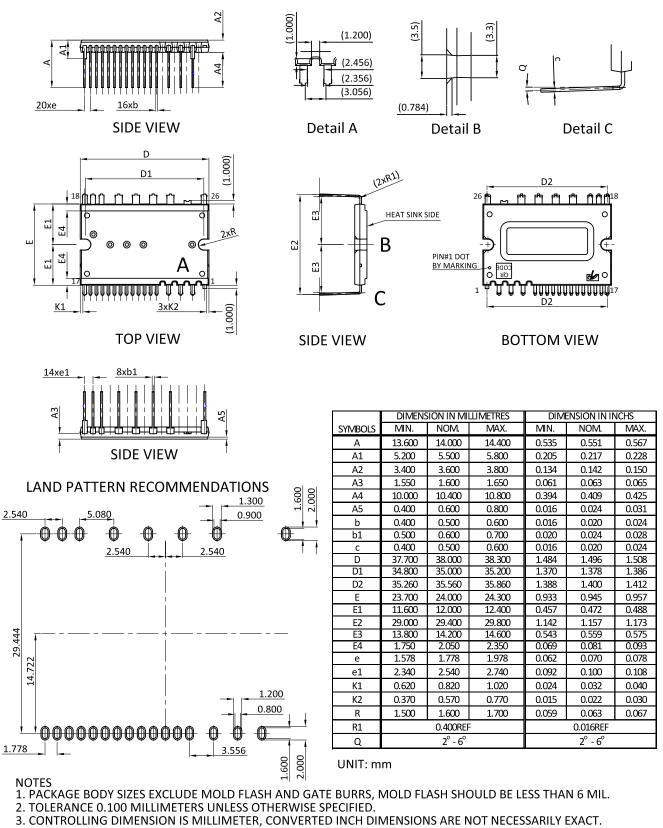






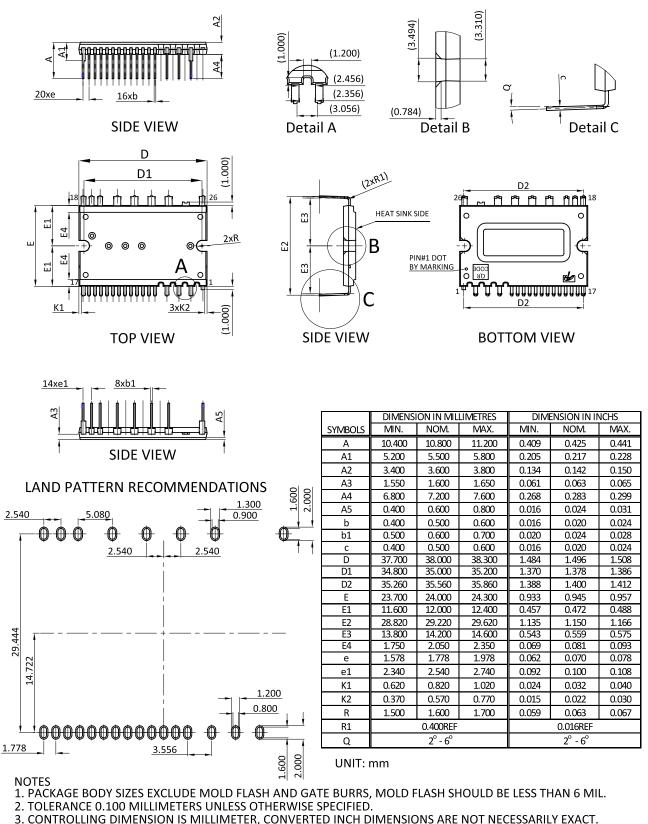


IPM-3: Long Terminal Type



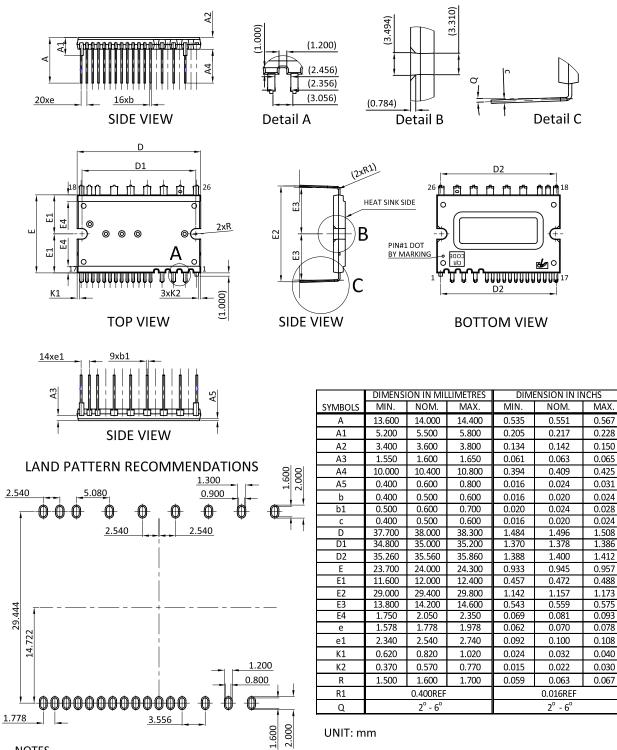


IPM-3A: Normal Terminal Type





IPM-3B: Long Terminal Type with PFC Diode



NOTES

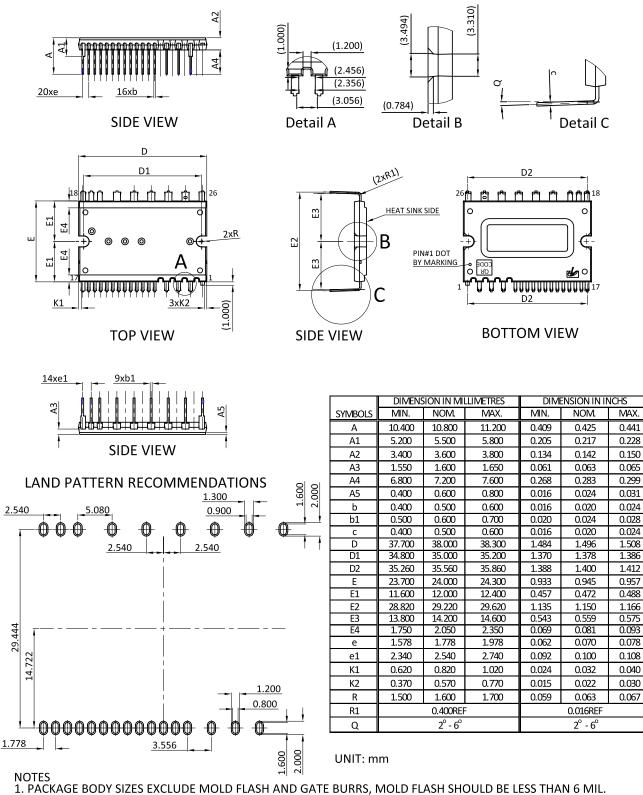
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.

2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.

3. CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



IPM-3C: Normal Terminal Type with PFC Diode



2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.

CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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